### MACROPOROUS SILICON DEEP UV FILTERS

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#### **Outline**

- Introduction and Rationale
- Physical basis of filtering in Macroporous silicon membranes
- Macroporous Silicon chemistry and fabrication
- Brief process flow diagram
- ALD coating description
- Experimental results
- Conclusions
- IR and other applications

## **Existing technology**

#### ABSORPTION-BASED

- Not suitable for deep UV range
- •Available materials absorb across entire deep UV spectrum

#### **INTERFERENCE-BASED**

- Limited width of the rejection bands;
- Poor physical longevity and lack of environmental stability (deep UV filters)
- Strong angular dependence of the pass band or rejection edge position



# Transmission mechanism through an uncoated MPSi array

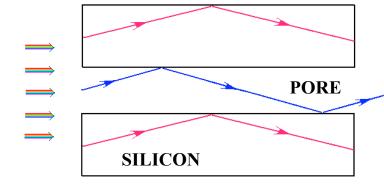
- Up to 700-900nm- transmission through the pore leaky waveguide array
- From 700-900nm to  $\sim 5\Lambda$  transmission through the Si host waveguide array
- $5\Lambda$  and above- transmission through an "effective medium"

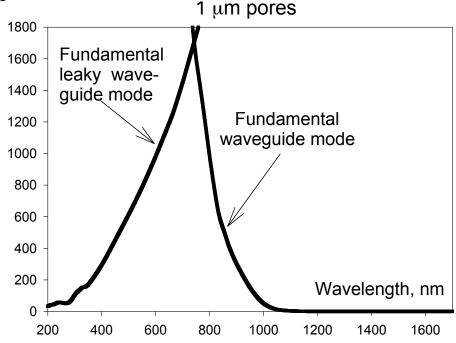
#### **UV-visible range:**

$$\alpha = f_0 \lambda^2 / d^3$$

$$\lambda_{-3dB} = \sqrt{\ln(2) \cdot \frac{d^3}{f_0 \cdot L}} \quad \lambda_{-20dB} = \sqrt{\ln(100) \cdot \frac{d^3}{f_0 \cdot L}}$$

## Sharpness and position of the rejection edge are bounded!



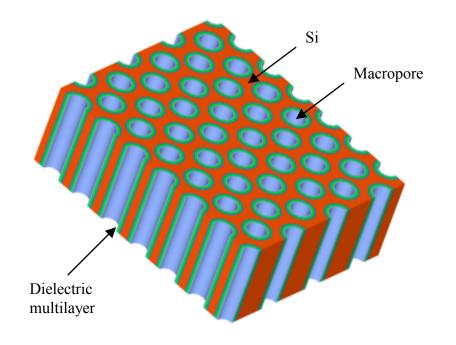


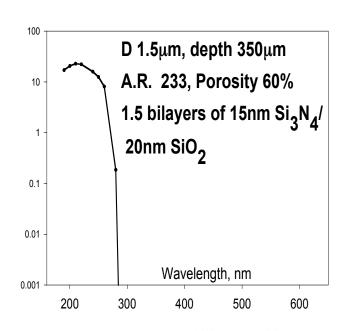
LakeShore.

Formulas taken from [I. Avrutsky and V. Kochergin, Appl. Phys. Lett., 82, 3590 (2003)]

## **Coated MPSi arrays**

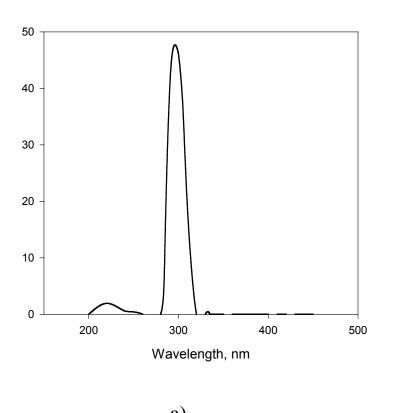
- Leaky mode losses can be selectively adjusted.
- High rejection levels are predicted.
- Transmission down to far and extreme UV is possible.
- Spectral position and shape of passand rejection bands are independent on angle of incidence.
- Far fewer layers are necessary in order to achieve a comparable edge sharpness and rejection level than in common interference filters.
- Filters are much more environmentally and thermally stable.

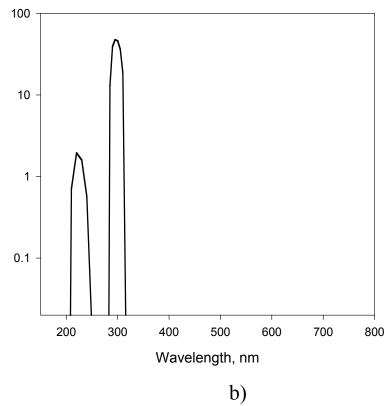






## Design (narrow bandpass filter)

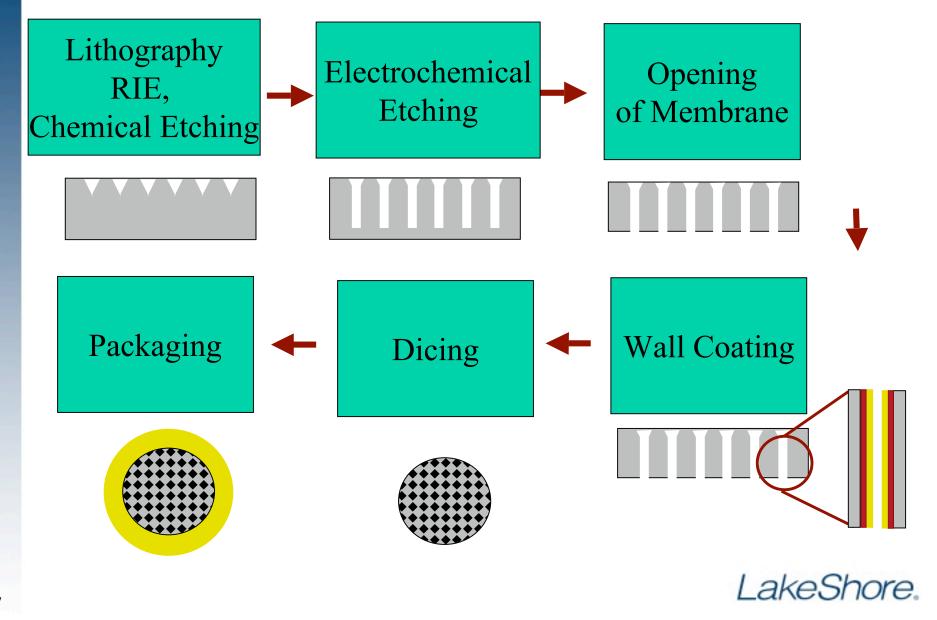




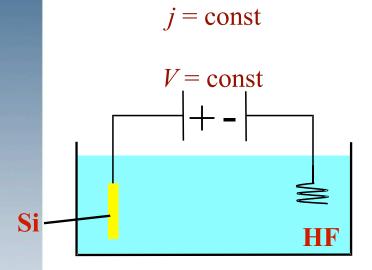
Numerically calculated spectral dependences of the transmission through an MPSi membrane with a 19-layer pore wall coating designed as a narrow bandpass filter, with band centered at 300nm. The transmission in a) is plotted on a linear scale, while in b) is given on a logarithmic scale.

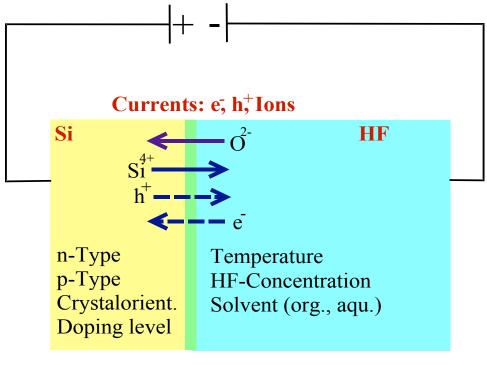


#### **Process flow**



### Porous silicon etching





#### Interface:

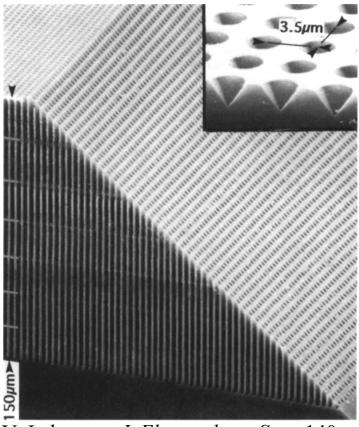
- Porous Silicon
- (Electropolishing can occur)

n-Si: Current limitation by hole supply Illumination of the silicon is necessary.



## Porous silicon etching (continuation)

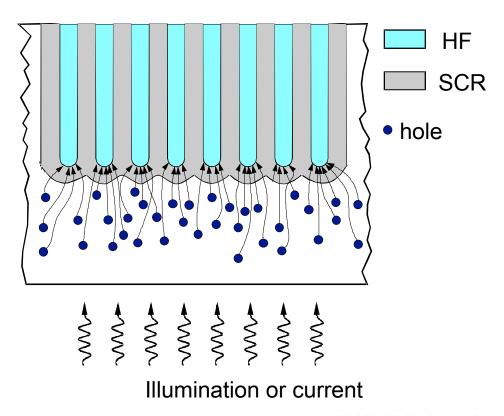
V. Lehmann, H. Föll, *J. Electrochem. Soc.*, 137, 653 (1990)



V. Lehmann, *J. Electrochem. Soc.*, 140, 2836 (1994)

#### Macropores in silicon

- space charge region around macropores
- photo (or electrical) generation of holes
- holes are minority carriers



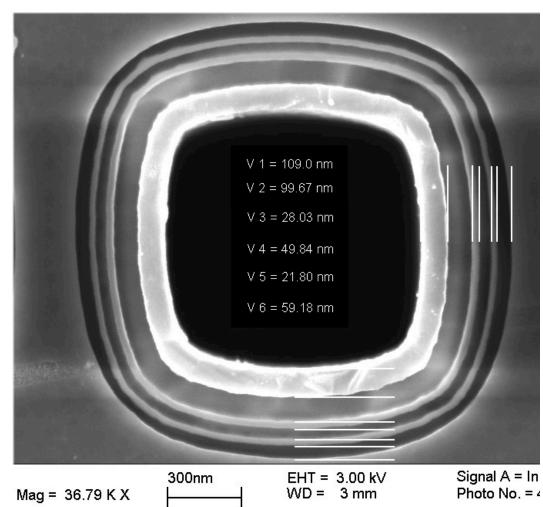


Multilayer coating of the pore walls

(LPCVD)

**Coating of MPSi** structure is demonstrated

- •Coating is not uniform
- •High stresses
- Very limited choice of materials



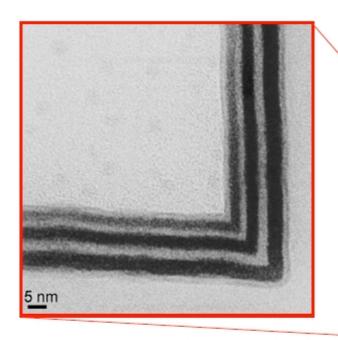
LPCVD pore wall coating and SEM images done by MEMS PI. www.memspi.com



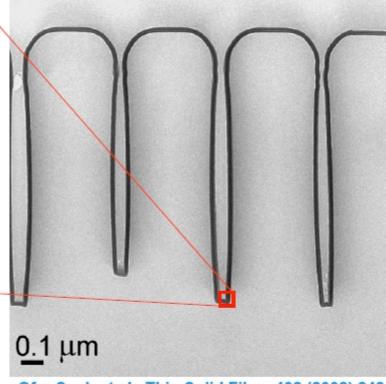
## **Atomic layer deposition (ALD)**

ALD - Atomic Level Precision - 100% Conformal Films





Nano-Layered Films



Ofer Sneh et al., Thin Solid Films 402 (2002) 248



Sundew Technologies, LLC - Proprietary For disclosure to BAE by LakeShore Cryotronics

LakeShore.

## **ALD** (continuation)

#### ALD - Atomic Level Precision - 100% Conformal Films

- ALD is inherently 100% conformal
- The key is the layer-by-layer growth
- Transport time into high aspect ratio structures is fast (~100 msec/mm)
- The challenge is chemical delivery. For example, 8" DRAM wafer (70 nm generation) requires 6×10<sup>18</sup> precursor molecules per dose !!!
- An Ultra High Area (UHA) substrate such as a porous silicon membrane requires 6×10<sup>19</sup> precursor molecules per dose !!! ⇒
   87 grams of trimethylaluminum per 1 µm of film! (\$50 per technical grade precursor)

Several dozens of different coatings (metals, semiconductor and dielectrics) have been demonstrated

Manual LL
chamber

Gas box

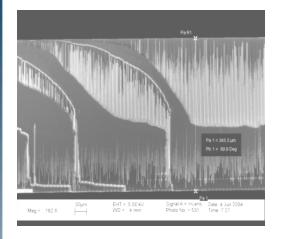
QDP40

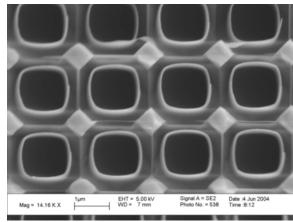
Instruments

Sundew Technologies

SMFD - ALD: 8" wafer prototype

## **Coating uniformity**





Good quality layers (granular structure was not observed)

Better than 5% for Al<sub>2</sub>O<sub>3</sub>

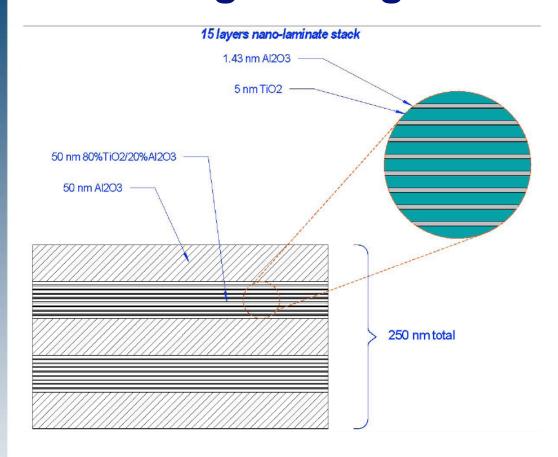
**→** 

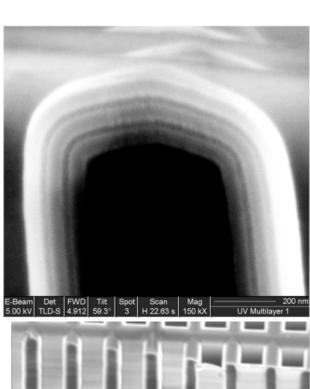
**82nm** 

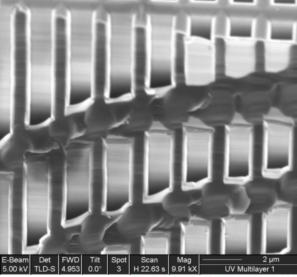
HfO<sub>2</sub> trials were not successful



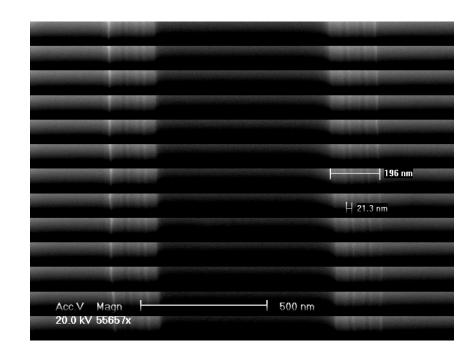
Nanolaminated stacks and refractive index engineering

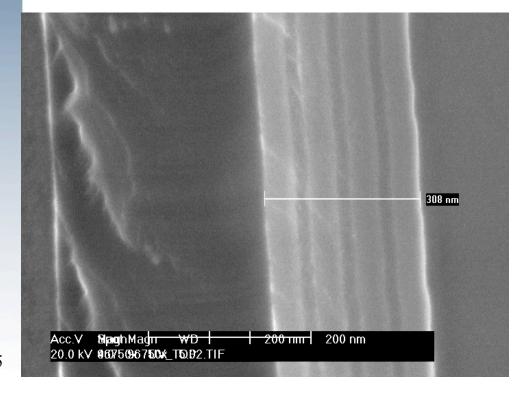






## 5-layer TiO2/Al2O3 ALD coating (ALD)

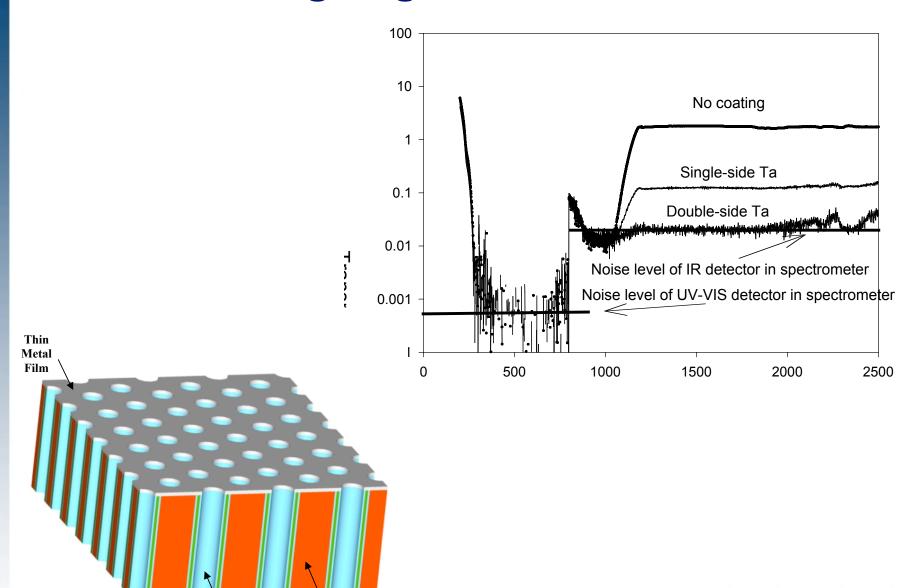




7-layer TiO2/Al2O3 ALD coating (ALD)



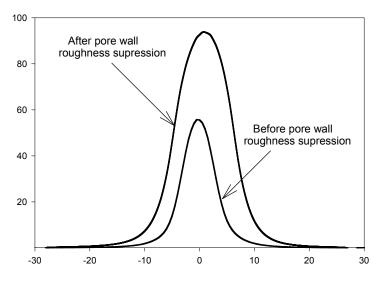
## Wide blocking, higher than 5 OD



**Multilayer** Coated Pores

Near field transmission efficiency exceeds 50% within the pass

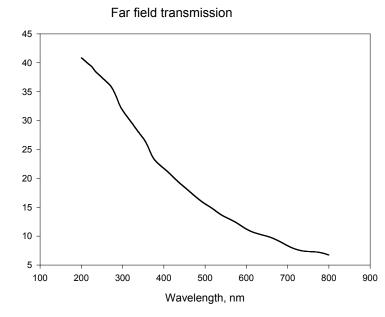
band



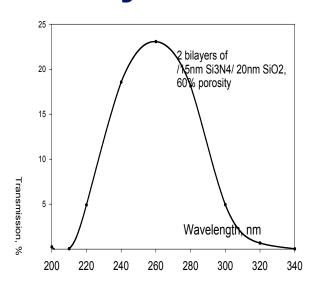
Far field transmission efficiency exceeds 30% within the pass

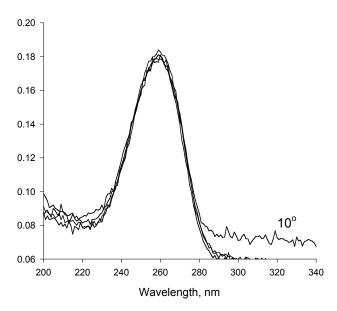
band

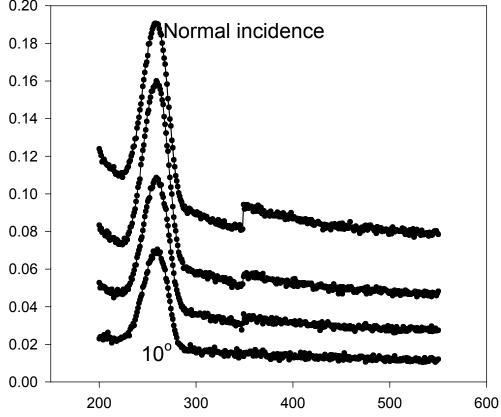




Optical testing of MPSi layer with multilayer coating 0.20 \_\_\_\_\_









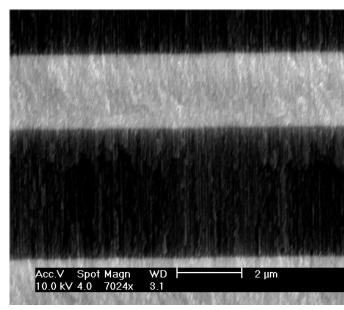
#### **Conclusions**

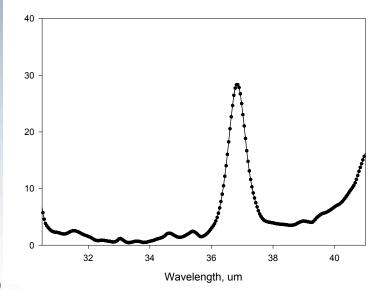
- •Pore formation process meet the requirements.
- •Feasibility of ALD pore wall coating is demonstrated for Al2O3 single layer and a Al<sub>2</sub>O<sub>3</sub>/TiO<sub>2</sub> nanolaminated stack. Attempts at HfO<sub>2</sub> deposition have failed so far. No functional filter fabricated.
- •Good agreement between theory and experiment. Good understanding of what's happening and what needs to be done.
- •For further progress, an ALD machine <u>at Lake Shore</u> is required.



# IR porous mesoporous silicon filters and mirrors

Consist of a porous silicon multilayer composed of alternated high-porosity/low porosity layers.

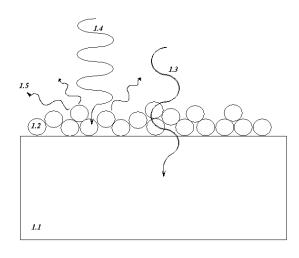




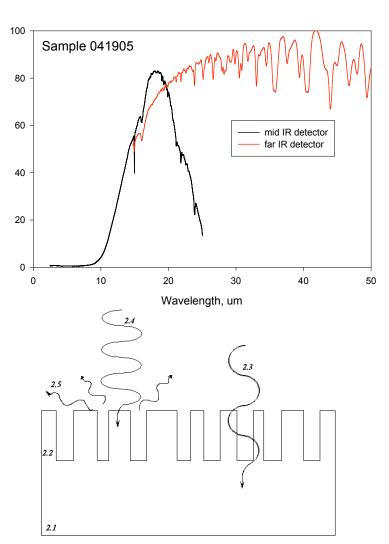


## IR long wave pass filters

- •Random MPSi layers
- •Light <u>scattering</u> is the key
- •Used as a part of almost any band-pass filter



Scattering by applied particles



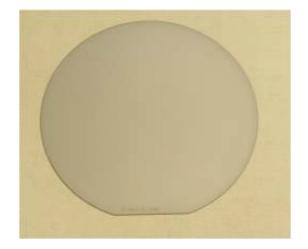
Scattering by random pores



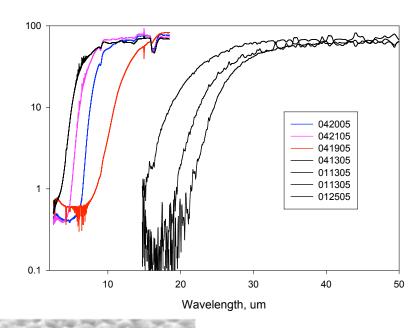
## IR long wave pass filters (continuation)



Glancing angle reflection, 100mm wafer



Normal to wafer surface



Pore layer cross section



## **UV** polarization components

